



November 11, 2010

## **RFMD Unveils High-Performance 2.3-2.7 GHz Power Amplifier IC for WiFi, WiMAX, LTE and Other Wireless Applications**

GREENSBORO, N.C., Nov. 11, 2010 (GLOBE NEWSWIRE) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, today unveiled the RF5632, a 2.3—2.7 GHz power amplifier IC. The RF5632 is optimized specifically for WiMAX systems and can be designed into multiple applications, including customer premises equipment (CPE), gateways, access points, LTE wireless infrastructure, and WiFi-based wireless high definition interface (WHDI) for wireless video distribution networks.

The RF5632 offers global customers a broadly applicable power amplifier IC featuring a powerful combination of industry-leading RF performance and best-in-class product size and ease-of-use. The RF5632 integrates a 3-stage PA and power detector into an industry-leading 4mm x 4mm QFN package, significantly minimizing customer design footprint requirements. Additionally, the RF5632 operates from a standard 5V supply, eliminating additional power supply requirements, enhancing design flexibility and lowering bill-of-material costs (BOM). The RF5632 is also fully DC and RF tested including EVM at the rated output power, maximizing application yields and accelerating time-to-market.

The RF5632 delivers an EVM of 2.5% and meets or exceeds WiMAX and LTE spectral mask requirements with an output power of 28dBm in the 2.3—2.4GHz, 2.4—2.5GHz, and 2.5—2.7GHz frequency ranges. The bias of the PA may be controlled to accommodate a 22dB gain step to increase the dynamic range of the system. The RF5632 offers high gain of 34dB and high linear output power, with best-in-class efficiency. The RF5632 maintains linearity over a wide range of temperatures and power outputs while the external match enables tuning for output power over multiple bands. The RF5632 also features internal input and inter-stage matching, a power-down mode and power detection. The RF5632 features InGaP HBT semiconductor technology and is packaged in a leadless chip carrier with a backside ground.

RFMD is showcasing the RF5632 and other industry-leading RF components at the electronica 2010 trade show in Munich Germany, November 9 through November 12. Product brochures are available at the RFMD booth (#A4.136), and datasheets can be obtained via RFMD's website at [www.rfmd.com](http://www.rfmd.com) or by contacting RFMD at 336-664-1233.

### **Availability**

The RF5632 starts at \$3.10 per 10,000 units. Samples and production quantities are available now through RFMD's online store or through local RFMD sales channels.

### **About RFMD**

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance semiconductor components. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at [www.rfmd.com](http://www.rfmd.com).

The RF Micro Devices, Inc. logo is available at <http://www.globenewswire.com/newsroom/prs/?pkgid=6436>

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and

uncertainties, including variability in operating results, risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, our reliance on a few large customers for a substantial portion of our revenue, the rate of growth and development of wireless markets, our ability to bring new products to market, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on gallium arsenide (GaAs) for the majority of our products, dependence on third parties, and substantial reliance on international sales and operations. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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Source: RF Micro Devices

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